

In the Specification:

[0031] Pad 100 has polishing layer 120 that has not been buffed or sanded down a distance D1 of 4 to 6 mils (0.1 to 0.15 mm) prior to being placed on platen 110 of polishing apparatus 115. Rather, pad 100 is placed on platen 110 without any surface removal or preparation. Cutting tool 118, such as a diamond polishing-conditioning head, is then placed in contact with surface 130. Cutting tool 118 is then activated (i.e., moved relative to surface 130 while contacting the surface) to remove only a small amount of surface material from top layer 120. In an example embodiment, top layer 120 is buffed down from its original surface 130 a distance D2 of less than 4 mils (0.1 mm). Most advantageously, the distance D2 is between 0.5 and 1.5 mils (0.012 to 0.038 mm). This in-situ removal results in a polishing surface 230 having a relatively high pore count of between 500 and 2,500 pores per mm².

Example